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## Numerical Modeling and Optimization of CaZrS3 chalcogenide Perovskite Solar Cell by Using SCAPS-1D with theoretical efficiency approaching 20%

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## 1. Introduction

Chalcogenide perovskites ABX3 (A=Alkaline earth metals; B=Transition metals; X=S or Se) have recently been studied, but they still need to be rigorously tested under various conditions. Several experimental studies on these materials have been conducted [1] [2]. Zr-based chalcogenide perovskites (AZrS3, where A is an alkaline earth metal such as Ca, Sr, or Ba) have a d-orbital character, whereas the 4d states are less localized than the 3d states, resulting in a high absorption coefficient and a low effective mass of the charge carriers in these compounds [3].

In this study, a device simulation of CaZrS3 material is reported for the first time, which makes this new study interesting, using the one-dimensional solar cell capacitance simulator SCAPS-1D. Therefore, we tried to propose low cost Electron Transport Materials ETMs (TiO2, ZnO, and SnO2). The influence of thickness, doping concentration (NA), and the working temperature on the device performance were studied.

## 1. Results

As a result, we have found that for CaZrS3 the most preferment structure is found to be: Au/NiOx/CaZrS3 (Absorber)/ZnO/FTO with a maximum PCE of 19.36%, V\_OC of 1.79 V, ⋈ J⋈\_SC of 16.13 mA/cm2 and FF of 89.85%.

## 1. References

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